TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7S14F, TC7S14FU

SCHMITT INVERTER

The TC7S14 is a high speed C²MOS SCHMITT INVERTER fabricated with silicon gate C²MOS technology. It achieves a high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

Pin Configuration and function are the same as the TC7SU04F but input have 25% V_{CC} hysteresis and with its schmitt trigger function, the TC7S14F can be used as line receivers which will receive slow input signal.

Input is equipped with protection circuits against static discharge or transinent excess voltage.

Output currents are 1/2 compared to TC74HC series models.

FEATURES

- High Speed $t_{pd} = 11ns$ (Typ.) at $V_{CC} = 5V$
- Low Power Dissipation $I_{CC} = 1\mu A$ (Max.) at $Ta = 25^{\circ}C$
- High Noise Immunity V_H = 1.1V at

- Symmetrical Output Impedance ... |I_{OH}| = I_{OL} = 2mA
- Balanced Propagation Delays t_{pLH}≒t_{pHL}
- Wide Operating Voltage Range ... V_{CC (opr)} = 2~6V

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~7	V
DC Input Voltage	VIN	-0.5~V _{CC} +0.5	V
DC Output Voltage	Vout	-0.5~V _{CC} +0.5	V
Input Diode Current	ік	± 20	mA
Output Diode Current	Іок	± 20	mA
DC Output Current	Ιουτ	± 12.5	mΑ
DC V _{CC} /Ground Current	lcc	± 50	mA
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	- 65~150	°C
Lead Temperature (10s)	Тլ	260	°C



Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MARKING



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LOGIC DIAGRAM





-**S**>>

NC 1

IN A 2

GND 3

5 Vcc

4 OUT Y

TRUTH TABLE

А	Y
L	Н
Н	L

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	2~6	V
Input Voltage	VIN	0~V _{CC}	V
Output Voltage	VOUT	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBOL		TEST CONDITION			Ta = 25°C			Ta = −40~85°C		UNIT
				Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	
Positive Threshold Voltage	VP		_	2.0 4.5	1.0 2.3	1.25 2.7	1.5 3.15	1.0 2.3	1.5 3.15	v
Threshold Voltage				6.0	3.0	3.5	4.2	3.0	4.2	
Negative Threshold Voltage	V _N	_		2.0 4.5 6.0	0.3 1.13 1.5	0.65 1.6 2.3	0.9 2.0 2.6	0.3 1.13 1.5	0.9 2.0 2.6	v
Hysteresis Voltage	V _H		_	2.0 4.5 6.0	0.3 0.6 0.8	0.6 1.1 1.2	2.0 1.0 1.4 1.7	0.3 0.6 0.8	2.0 1.0 1.4 1.7	v
High-Level Output Voltage	Vou	V _{OH} V _{IN} = V _{IL}	I _{OH} = -20μA	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	— — —	v
	· OH		I _{OH} = – 2mA I _{OH} = – 2.6mA	4.5 6.0	4.18 5.68	4.31 5.80	_	4.13 5.63	_	
Low-Level Output Voltage VOL	Voi	V _{OL} V _{IN} = V _{IH}	l _{OL} = 20μA	2.0 4.5 6.0		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
			I _{OL} = 2mA I _{OL} = 2.6mA	4.5 6.0		0.17 0.18	0.26 0.26		0.33 0.33	
Input Leakage Current	IIN	V _{IN} = V _{CC} or GND		6.0	_	_	±0.1	_	± 1.0	μΑ
Quiescent Supply Current	lcc	V _{IN} = V _{CC} or GND		6.0			1.0		10.0	μΑ

Output currents are 1/2 compared to TC74HC series models.

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CHARACTERISTIC	SYMBOL	TEST CONDITION		Ta = 25°C					
CHARACTERISTIC	STIVIBUL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT			
Output Transition	tTLH			1	8				
Time	tthl	—		4	0	nc			
Propagation Delay	t _{pLH}			11	21	ns			
Time	t _{pHL}	—			21				

AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, $V_{CC} = 5V$, $Ta = 25^{\circ}C$)

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 pF$, Input $t_f = t_f = 6 ns$)

CHARACTERISTIC SYMB				Ta = 25°C			Ta = - 4		
CHARACTERISTIC	CHARACTERISTIC SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Output Transition t _{TLH} Time t _{THL}			—	50	125	—	145		
	_	4.5		14	25	—	30		
		6.0	_	12	21	—	24		
Propagation Delay t _{pLH} Time t _{pHL}	4		2.0	_	48	100	_	235	ns
		4.5		12	20		48		
	U VPHL		6.0		9	17	_	40	
Input Capacitance	CIN	_		—	5	10	—	10	
Power Dissipation	Con	Note (1)			28				pF
Capacitance C _{PD}				20					

Note (1) : C_{PD} is defined as the value of internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation : $I_{CC}(opr) = CPD \cdot V_{CC} \cdot f_{IN} + I_{CC}$